

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10377	(438/151,197,201,257,258,288,261,263).OCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 14:27
L2	5523	(257/314,315,321).OCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 14:27
L3	5260	(257/E21.422,E21.68,E21.683,E21.687,E21.688,E29.129,E29.3).OCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 14:28
L4	17214	1 or 2 or 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 14:28
L6	7773	(pattern\$4 or remov\$4 or etch\$4) same (oxide or nitride or ONO or oxide/nitride or oxide/nitride/oxide or O-N-O or oxide-nitride or oxide-nitride-oxide) same control same floating same gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 14:29

L7	3969	4 and 6	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 14:30
L11	2145	7 and (((@ad<"20011228") or (@riad<"20011228"))	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 14:31
L14	753141	(cell or memory or core) same (peripheral or periphery or logic or (high or low) near voltage) or HV or LV or NMOS or PMOS)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 14:36
L15	1461	11 and 14	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 14:36
L16	881	15 and (flash near memory)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 14:41
L17	23	("4833096" "4997777" "5216268" "5297082" "5326999" "5495441" "5554862" "5568422" "5610419" "5661057" "5675161" "5698879" "5780341" "5843796" "6001692" "6022779" "6027971" "6057194" "6057580" "6087706" "6103577" "6265266").PN. OR ("6673678").URPN.	US-PGRUB; USPAT; USOCR	OR	ON	2009/04/22 15:49

L18	40310	Hynix.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:36
L19	939364	Kim.in. or Jung.in. or Cho.in. or Lee.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:36
L20	432589	(pattern\$4 or etch\$4 or remov\$4) near8 (polysi or poly-si or polysilicon or poly-silicon or control or floating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:38
L21	77140	20 same (tunnel or dielectric or insulating or insulator or insulated or oxide or oxide-nitride-oxide or nitride or ONO or O-N-O)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:39
L22	17516	20 and 21 and 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:39
L23	460	18 and 22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:40

L24	225	23 and (flash near memory)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:40
L25	42	24 and (((@ad<"20011228") or (@rlad<"20011228"))	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 16:41
L26	6	("6005270").PN. OR ("6455374").URPN.	US-PGRUB; USPAT; USOCR	OR	ON	2009/04/22 16:43
L27	2138	19 and 22	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:45
L28	856	27 and (flash near memory)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:47
L29	211	28 and (((@ad<"20011228") or (@rlad<"20011228"))	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 16:47
L30	194	29 not 25	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 16:47

L33	39	((cell or memory) and peripheral and control and floating and (tunnel or dielectric or insulating or insulated or insulator) and oxide and nitride and ((pattern\$4 or etch \$4) near8 (control or conductive or polysi or poly-si or polysilicon or poly-silicon)) and (source or drain or S/D or source/drain)).clm.	US-PGPUB; USPAT	OR	ON	2009/04/22 17:03
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4/22/2009 5:10:12 PM

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